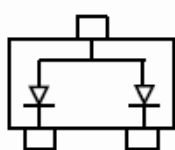


SWITCHING DIODE

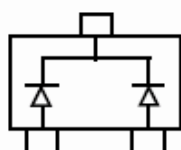
FEATURES

- Fast Switching Speed
- For General Purpose Switching Applications
- High Conductance

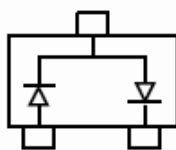
MARKING:



BAW56:A1



BAV70:A4



BAV99:A7

BAW56/BAV70/BAV99



MAXIMUM RATINGS (TA=25°C unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|--|------------|---------|------|
| Reverse voltage | V | 70 | V |
| Forward Current | I | 200 | mA |
| Peak Forward Surge Current | IFM(surge) | 500 | mA |
| Power Dissipation | P | 225 | mW |
| Thermal Resistance Junction to Ambient Air | R J | 556 | °C/W |
| Junction temperature | T | 150 | °C |
| Storage temperature range | TST | -55-150 | °C |

ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Conditions |
|-------------------------------|-----------------|------|------|-------|------|--|
| Reverse Breakdown Voltage | V R | 70 | | | V | IR=100µA |
| Forward voltage | VF1 | | | 0.715 | V | IF=1mA |
| | VF2 | | | 0.855 | V | IF=10mA |
| | VF3 | | | 1 | V | IF=50mA |
| | VF4 | | | 1.25 | V | IF=150mA |
| Reverse current | IR | | | 2.5 | µA | VR=70V |
| Capacitance between terminals | CT | | | 1.5 | pF | VR=0,f=1MHz |
| Reverse recovery time | t _{rr} | | | 6 | ns | IF = IR = 10mA, Irr= 0.1 x IR, RL = 100 |

BAW56/BAV70/BAV99 Typical Characteristics

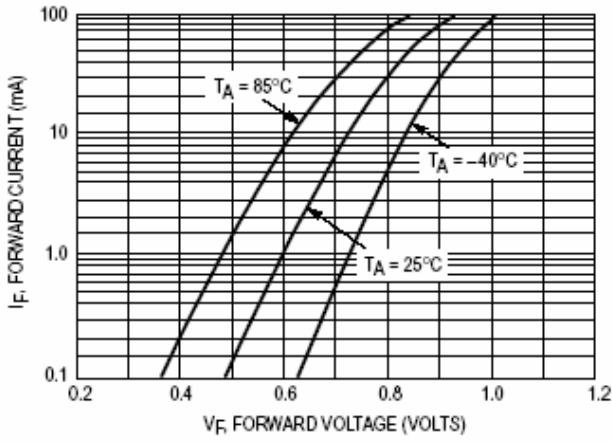


Figure 1. Forward Voltage

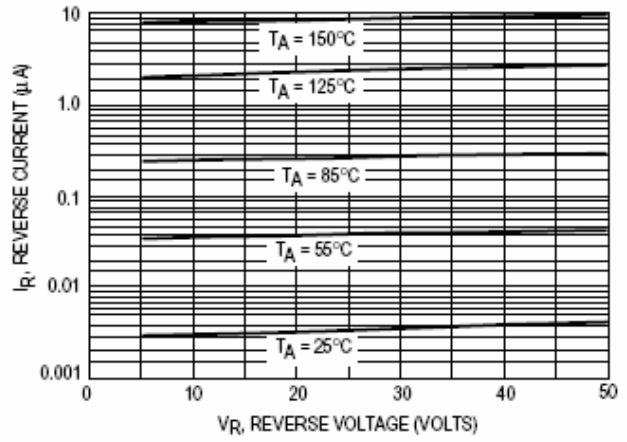


Figure 2 Leakage Current

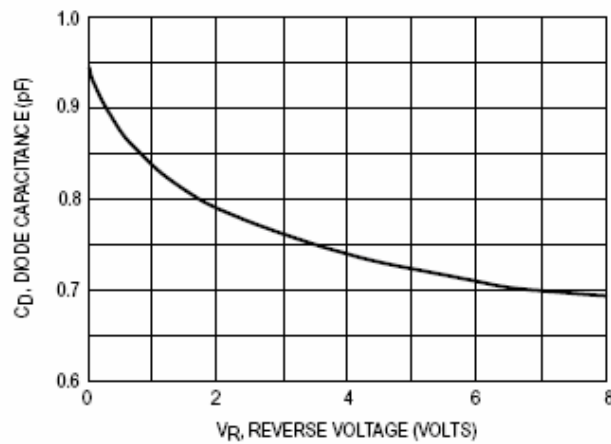


Figure 3 Capacitance